

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 plastic package. This very sensitive gate "series D" triac is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate
- Triggering in all four quadrants

3. Applications

- Air conditioner indoor fan control
- General purpose low power motor control
- General purpose switching and phase control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	12.5	A
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 51 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	1	Α
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2- G+;	-	-	7	mA
		T _j = 25 °C; <u>Fig. 7</u>				

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2—T1
2	G	gate	<u> </u>	Sym051
3	T1	main terminal 1	TO-92 (SOT54)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT131-600D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
BT131-600D/L01	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 51$ °C; Fig. 1; Fig. 2; Fig. 3	-	1	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	12.5	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	13.7	Α
l ² t	I2t for fusing	$t_p = 10 \text{ ms; SIN}$	-	0.78	A ² s
dl _T /dt	rate of rise of on-state current	I _G = 10 mA; T2+ G+	-	50	A/µs
		I _G = 10 mA; T2+ G-	-	50	A/µs
		I _G = 14 mA; T2- G+	-	10	A/µs
		I _G = 10 mA; T2- G-	-	50	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

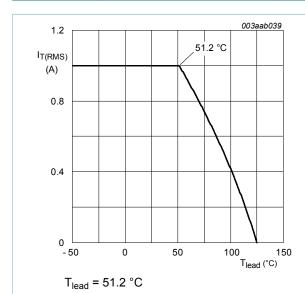
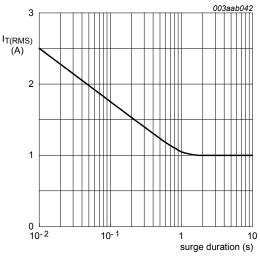


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; $T_{lead} = 51.2 \text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

BT131-600D

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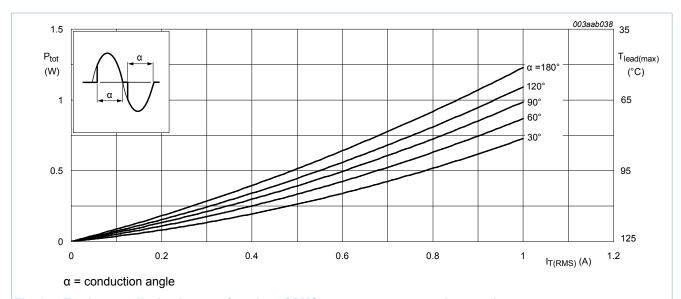


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

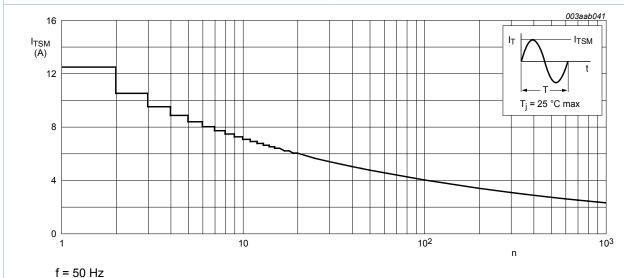
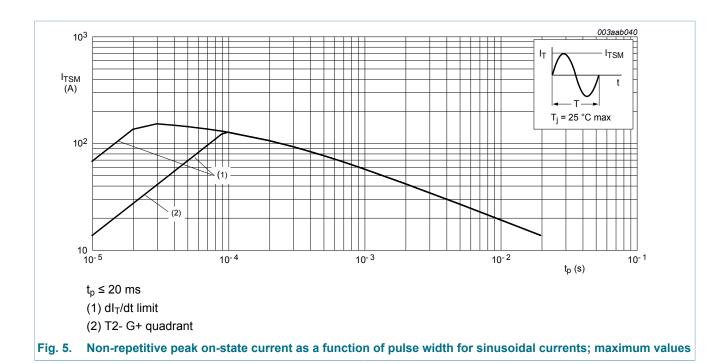


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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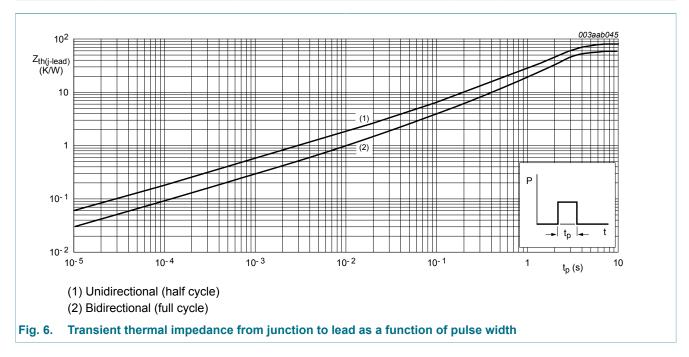


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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
		half cycle; Fig. 6	-	-	80	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board mounted: lead length 4 mm	-	150	-	K/W



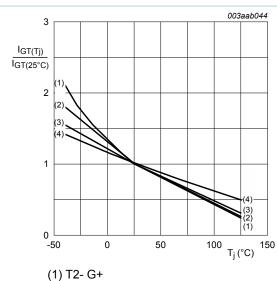
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	7	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	10	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; <u>Fig. 8</u>	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	1.3	10	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.2	0.3	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic o	characteristics		, , , , , , , , , , , , , , , , , , ,			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GT1} = 1 kΩ; (V_{DM} = 67% of V_{DRM}); exponential waveform	20	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 125 °C; dI_{com} / dt = 0.5 A/ms; I_T = 1 A; gate open circuit	3	-	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 1.5 A; V_D = 600 V; I_G = 0.1 A; $dI_G/$ dt = 5 A/ μ s	-	2	-	μs

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- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

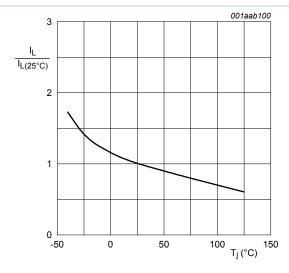
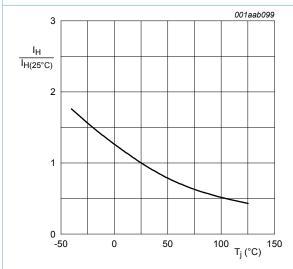
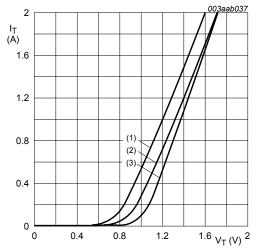


Fig. 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of junction temperature



 $V_0 = 0.92 \text{ V}; R_s = 0.4 \Omega$

- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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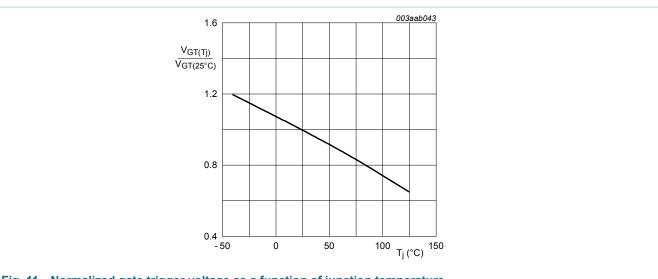


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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10. Package outline

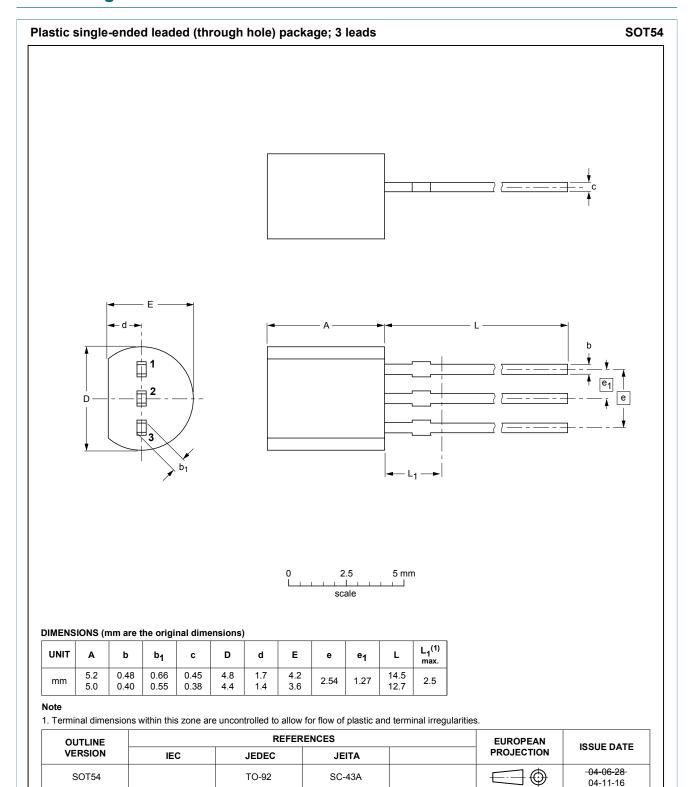


Fig. 12. Package outline TO-92 (SOT54)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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